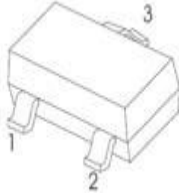
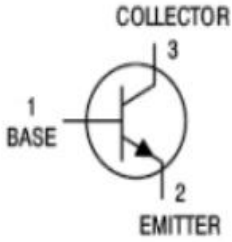


TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors																																										
<p><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p>	<p>Features</p> <ul style="list-style-type: none"> • For general AF applications • High collector current • High current gain • Low collector-emitter saturation voltage • Complementary types: BC807 (PNP) 																																										
<p>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</p> <table border="1"> <thead> <tr> <th>Parameter</th> <th>Symbol</th> <th>Value</th> <th>Unit</th> </tr> </thead> <tbody> <tr> <td>Collector-Base Voltage</td> <td>VCBO</td> <td>50</td> <td>V</td> </tr> <tr> <td>Collector-Emitter Voltage</td> <td>VCEO</td> <td>45</td> <td>V</td> </tr> <tr> <td>Emitter-Base Voltage</td> <td>VEBO</td> <td>5</td> <td>V</td> </tr> <tr> <td>Collector Current -Continuous</td> <td>IC</td> <td>500</td> <td>mA</td> </tr> <tr> <td>Collector Current -Pulsed</td> <td>ICM</td> <td>200</td> <td>mA</td> </tr> <tr> <td>Collector Power Dissipation</td> <td>PC</td> <td>300</td> <td>mW</td> </tr> <tr> <td>Thermal Resistance From Junction To Ambient</td> <td>RθJA</td> <td>417</td> <td>°C/W</td> </tr> <tr> <td>Junction Temperature</td> <td>Tj</td> <td>150</td> <td>°C</td> </tr> <tr> <td>Storage Temperature</td> <td>Tstg</td> <td>-55~+150</td> <td>°C</td> </tr> </tbody> </table>				Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	50	V	Collector-Emitter Voltage	VCEO	45	V	Emitter-Base Voltage	VEBO	5	V	Collector Current -Continuous	IC	500	mA	Collector Current -Pulsed	ICM	200	mA	Collector Power Dissipation	PC	300	mW	Thermal Resistance From Junction To Ambient	RθJA	417	°C/W	Junction Temperature	Tj	150	°C	Storage Temperature	Tstg	-55~+150	°C
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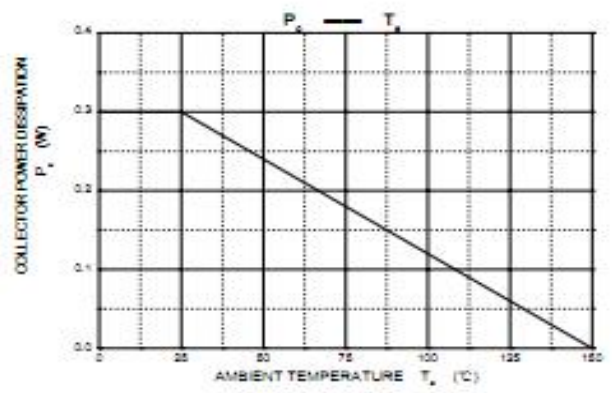
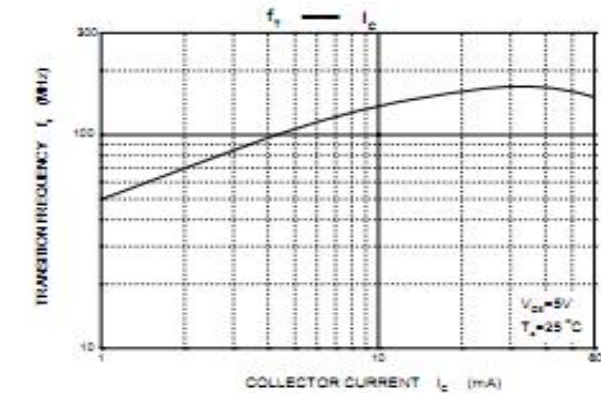
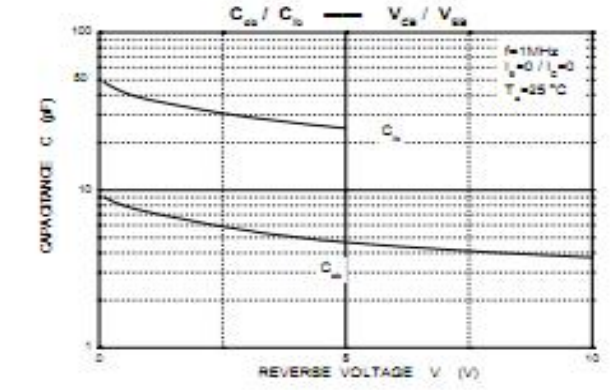
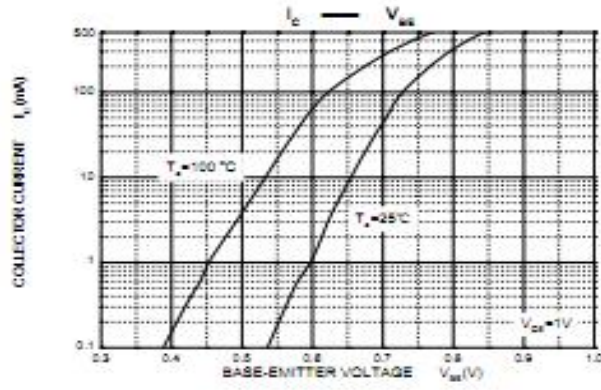
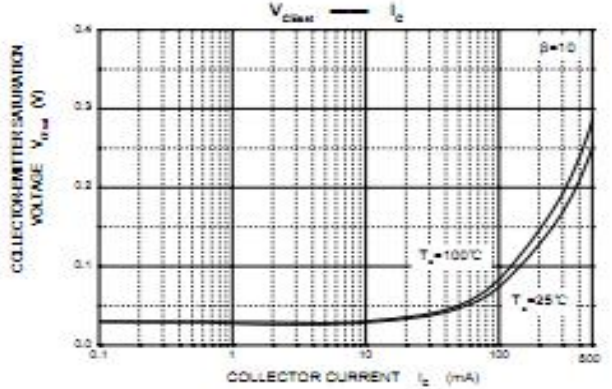
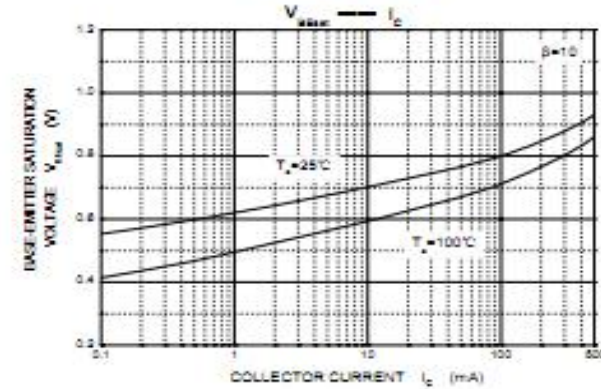
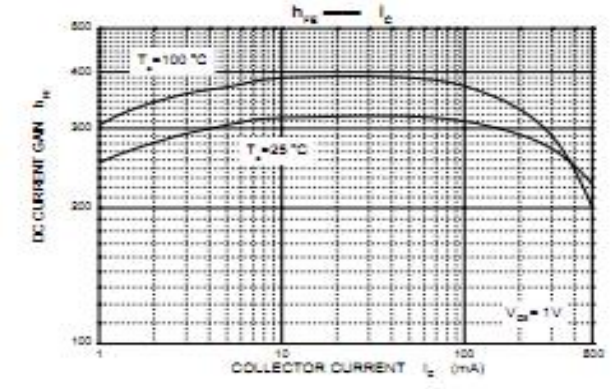
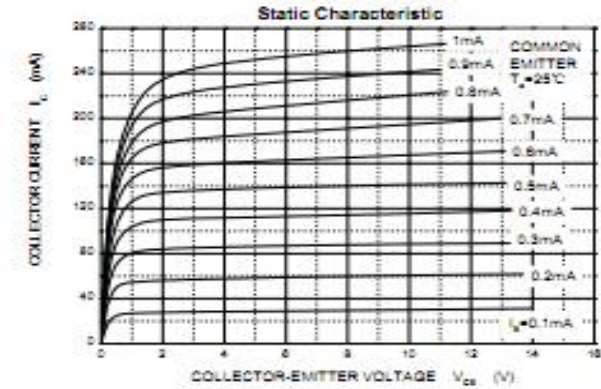
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 10μA, IE=0	50			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	45			V
Emitter-base breakdown voltage	V(BR)EBO	IE=10μA, IC=0	6			V
Collector cut-off current	ICBO	VCB= 45 V , IE=0			0.1	μA
Collector cut-off current	ICEO	VCB= 40V , IE=0			0.8	μA
Emitter cut-off current	IEBO	VEB= 5V , IC=0			0.1	μA
DC current gain	hFE	VCE= 1V, IC= 100mA	100		600	
	hFE	VCE= 1V, IC= 500mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC= 500mA, IB= 5mA			0.65	V
Base-emitter saturation voltage	VBE(sat)	IC= 500 mA, IB= 5mA			1.2	V
Transition frequency	fT	VCE= 5V, IC= 10mA f=100MHz	100			MHz
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz		10		PF

CLASSIFICATION OF hFI

Rank	BC817-16	BC817-25	BC817-40
Range	100-250	160-400	250-600
Marking	6A	6B	6C

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)